N-Channel Super Junction Power MOSFET Ⅳ

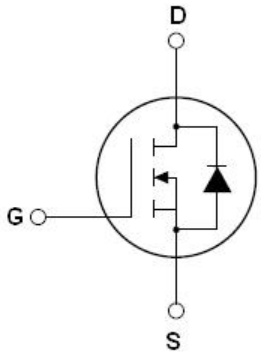
General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode.This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications,Fast charger, new energy vehicle charging pile, on-board OBC etc.

$V_{DS\ min@Tjmax}$	710	V
$R_{DS(ON)TYP}$	85	mΩ
ID	36	A
Qg	55	nC

Features

- ●New technology for high voltage device
- ●Ultra low on-resistance and ultra low conduction losses
- ●Ultra Low Gate Charge cause lower driving requirements
- ●Diode reverse recovery speed is super fast
- ●High reliability
- ●ROHS compliant



Schematic diagram

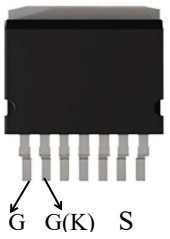
Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）
- On-board charger(OBC)

✧ **Intrinsic fast-recovery body diode**

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF099D7	TO-263-7L	NCE65NF099D7



TO-263-7L

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	650	V
Gate-Source Voltage (V_{DS}=0V) AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (V_{DS}=0V) DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	36	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	25.2	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	108	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	346 2.30	W W/°C
Single pulse avalanche energy **(Note 2)**	E_{AS}	484	mJ
Avalanche current**(Note 1)**	I_{AR}	11	A
Repetitive Avalanche energy ， t_{AR} limited by T_{jmax} **(Note 1)**	E_{AR}	3.9	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.43	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=1mA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			400	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=500uA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=18A		85	99	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		2800	3200	pF
Output Capacitance	C_{oss}			96		pF
Reverse Transfer Capacitance	C_{rss}			6		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=18A, V_{GS}=10V		55	60	nC
Gate-Source Charge	Q_{gs}			16.5		nC
Gate-Drain Charge	Q_{gd}			25.5		nC
Gate plateau voltage	Vgp			7.3		V
Intrinsic gate resistance	R_G	f = 1 MHz open drain		4		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=18A, R_G=1.7Ω,V_{GS}=10V		15		nS
Turn-on Rise Time	t_r			14		nS
Turn-Off Delay Time	$t_{d(off)}$			72		nS
Turn-Off Fall Time	t_f			14		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			36	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				108	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=36A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=18A,di/dt=100A/μs		160		nS
Reverse Recovery Charge	Q_{rr}			0.96		uC
Peak Reverse Recovery Current	I_{rrm}			12		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

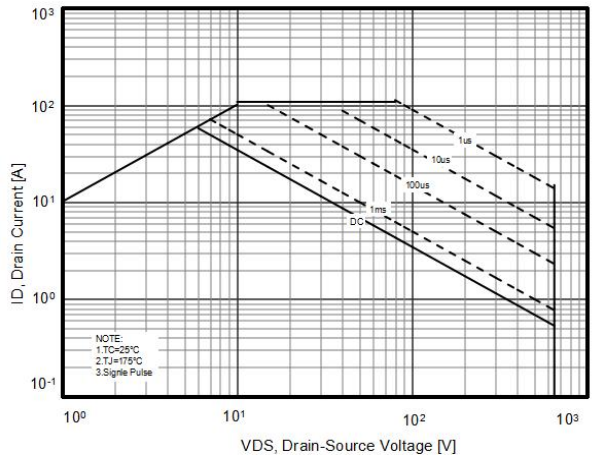


Figure2. Capacitance

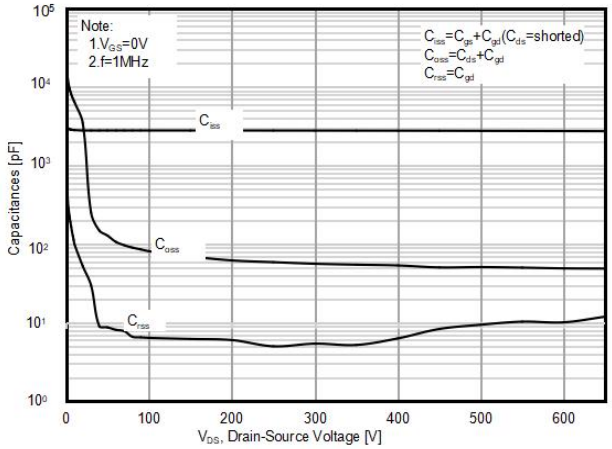


Figure3. Output characteristics

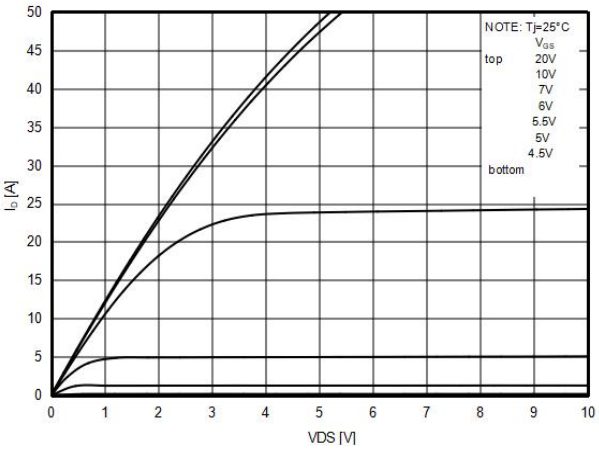


Figure4. Source-Drain Diode Forward Voltage

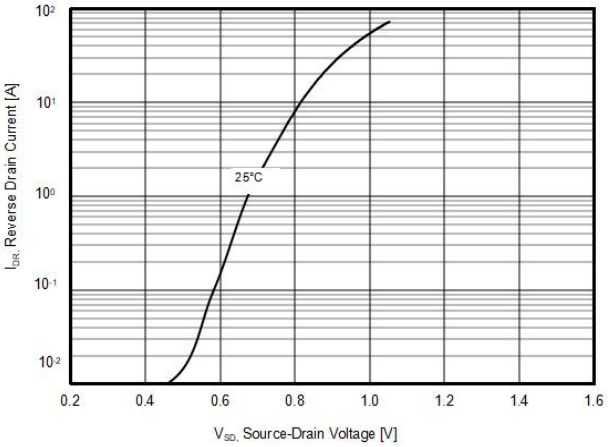


Figure5. Static drain-source on resistance

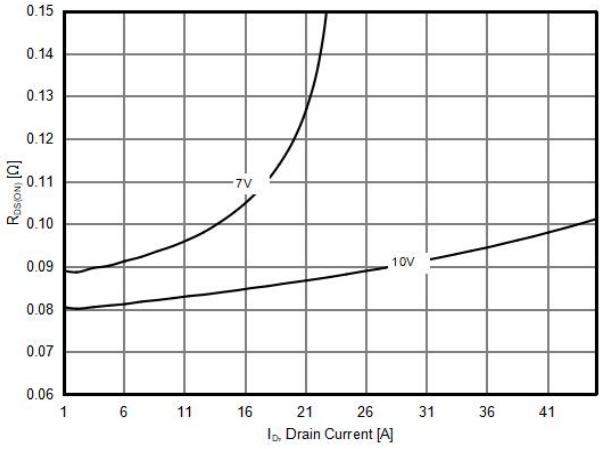


Figure6. Transfer characteristics

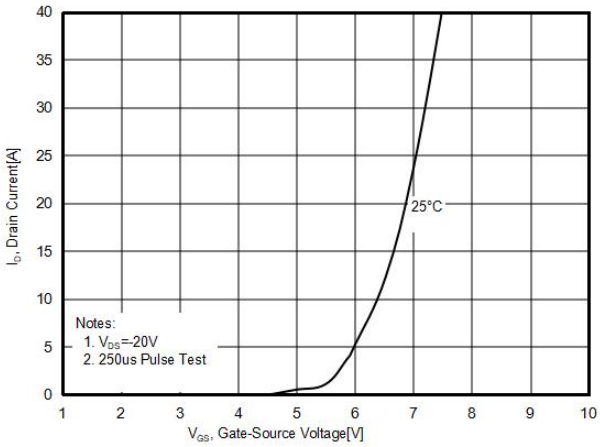


Figure7. $R_{DS(ON)}$ vs Junction Temperature

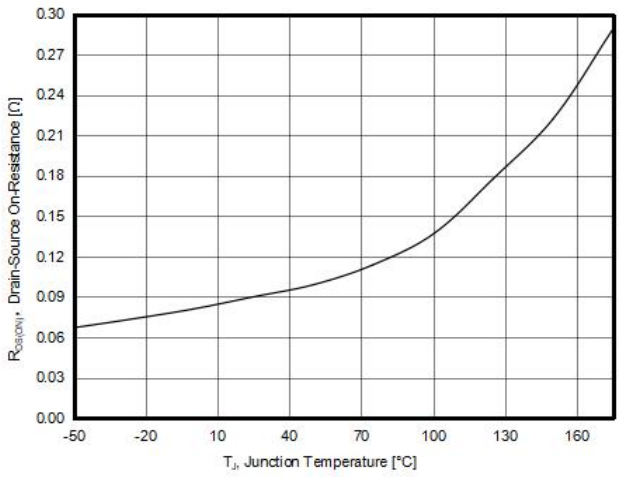


Figure8. BV_{DSS} vs Junction Temperature

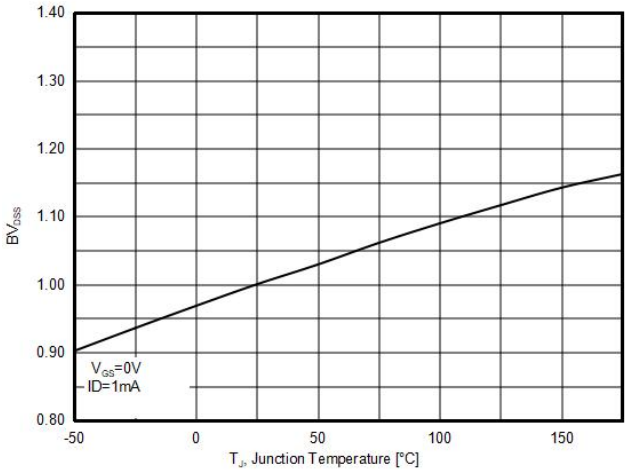


Figure9. Gate charge waveforms

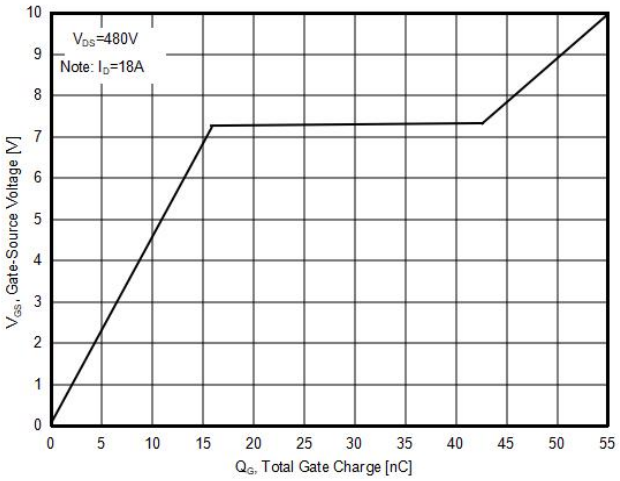
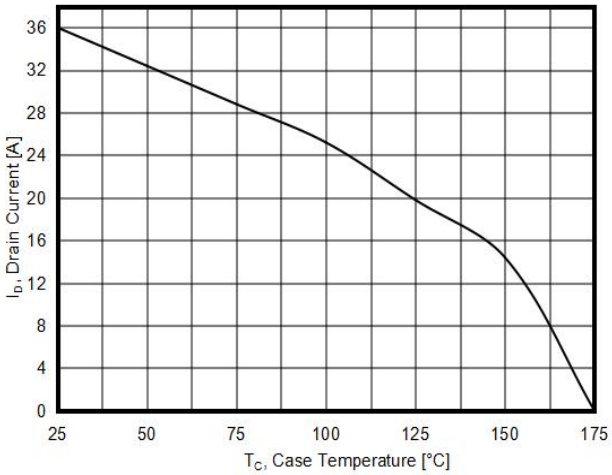
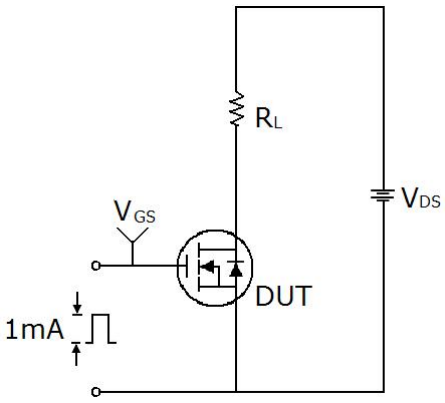


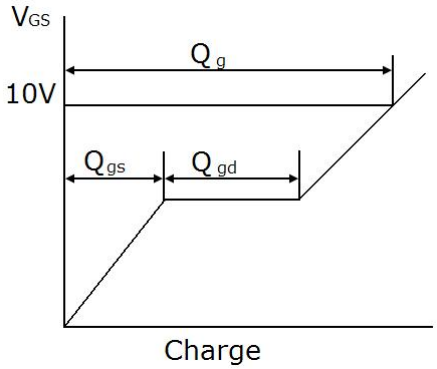
Figure10. Maximum I_D vs Junction Temperature



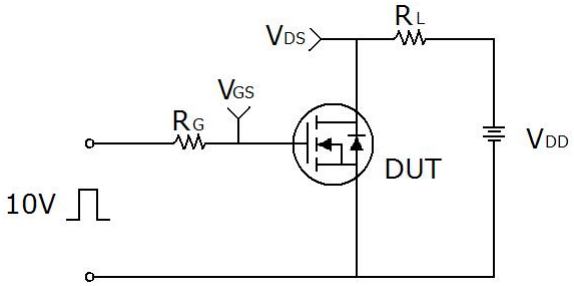
Test circuit

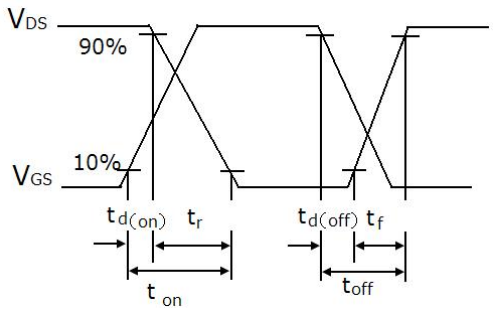
1）Gate charge test circuit & Waveform



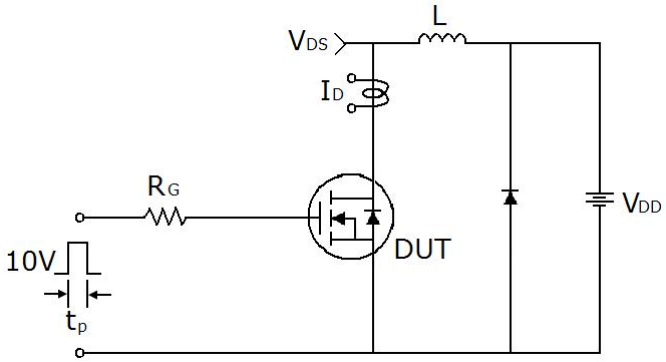


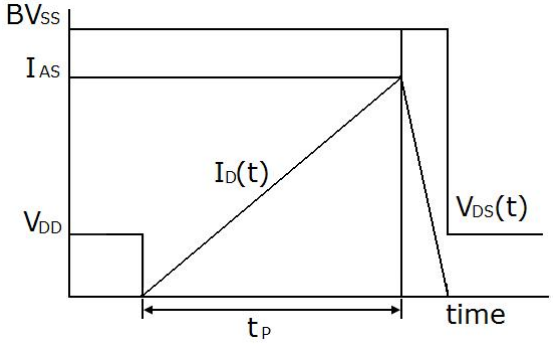
2）Switch Time Test Circuit：



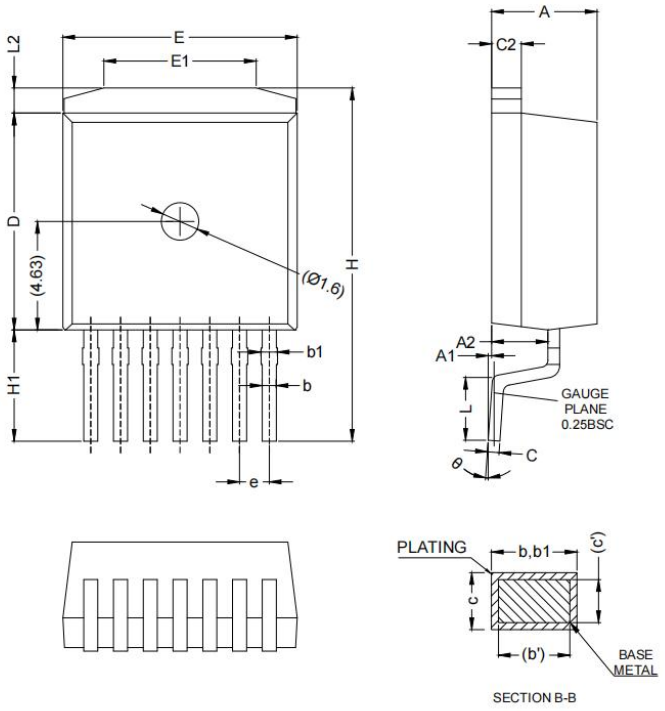


3）Unclamped Inductive Switching Test Circuit & Waveforms





TO-263-7L （B）Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A1	-	0.25		0.010
A2	2.20	2.60	0.087	0.102
b	0.52	0.72	0.020	0.028
b'	0.50	0.70	0.020	0.028
b1	0.60	0.80	0.024	0.031
c	0.42	0.62	0.017	0.024
c'	0.40	0.60	0.016	0.024
c2	1.07	1.47	0.042	0.058
D	9.05	9.45	0.356	0.372
D1	7.58	7.98	0.298	0.314
D2	2.05	2.45	0.081	0.096
e	1.27BSC		1.27BSC	
E	9.80	10.20	0.386	0.402
E1	6.30	6.70	0.248	0.264
E2	7.80	8.20	0.307	0.323
L	2.48	2.88	0.098	0.113
L2	0.87	1.27	0.034	0.050
H	14.87	15.27	0.585	0.601
H1	4.55	4.95	0.179	0.195

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